**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

# 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	7.5	Α
Static charact	Static characteristics						,
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 7.5 \text{ A}; T_j = 25 \text{ °C}$		-	16	20	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D I
2	D	drain	7 7 5	
3	G	gate		$G \left( \begin{array}{c} \downarrow \\ \downarrow \downarrow \end{array} \right)$
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa255
7	D	drain		
8	S	source		

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMPB20XNEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB20XNEA	3J

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
$V_{GS}$	gate-source voltage	-		-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	7.5	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	4.8	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	30	Α
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = 1.3 A; DUT in avalanche (unclamped)		-	13	mJ
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	460	mW
			[1]	-	1.65	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode				'	_
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.65	Α
ESD maxim	num rating		'		'	
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

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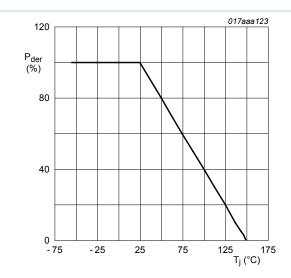


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

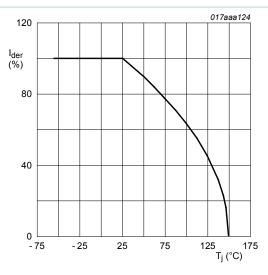


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

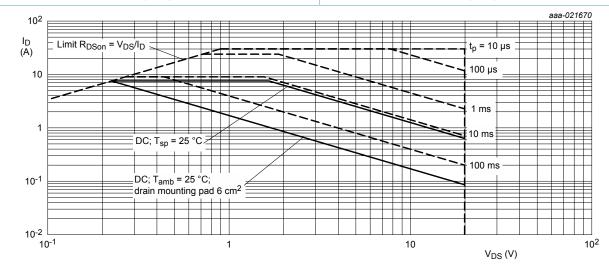


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	235	270	K/W
			[2]	-	67	74	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

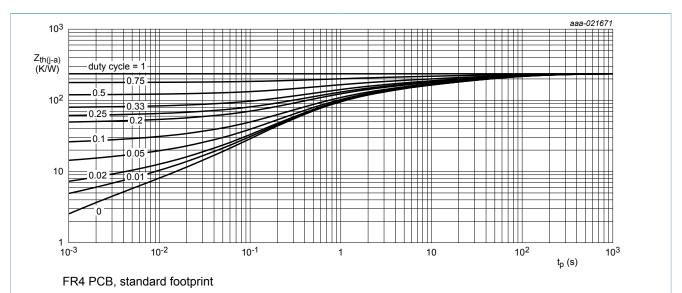


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

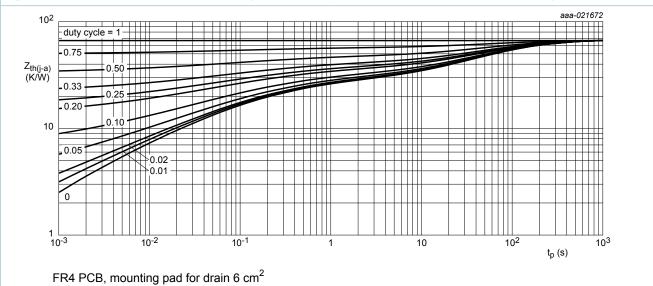


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.75	1	1.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		$V_{GS}$ = -12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μΑ
		$V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	5	μΑ
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-5	μΑ
		$V_{GS} = 2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS}$ = -2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
$R_{DSon}$	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 7.5 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	16	20	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 7.5 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	24	30	mΩ
		$V_{GS}$ = 2.5 V; $I_{D}$ = 6.1 A; $T_{j}$ = 25 °C	-	24	30	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 7.5 A; $T_{j}$ = 25 °C	-	26.8	-	S
$R_G$	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic c	haracteristics					
$Q_{G(tot)}$	total gate charge	$V_{DS} = 10 \text{ V}; I_D = 7.5 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	9.9	15	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	1.4	-	nC
$Q_{GD}$	gate-drain charge		-	3.1	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	930	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	178	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	144	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; $I_D$ = 7.5 A; $V_{GS}$ = 4.5 V;	-	16	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	40	-	ns
$t_{d(off)}$	turn-off delay time		-	44	-	ns
t <sub>f</sub>	fall time		-	22	-	ns
Source-dra	in diode				•	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 1.65 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.7	1.2	V

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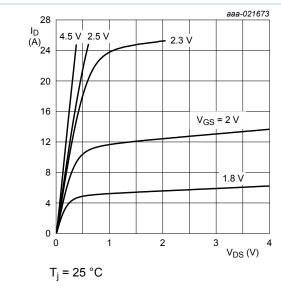


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

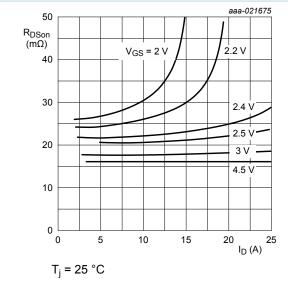


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

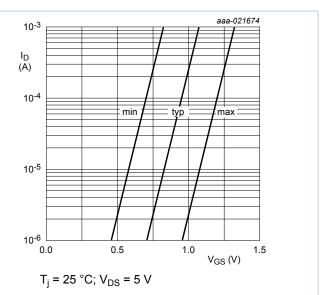


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

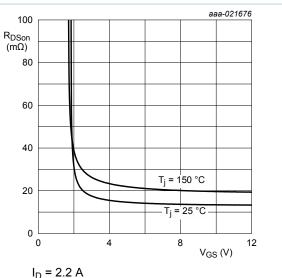


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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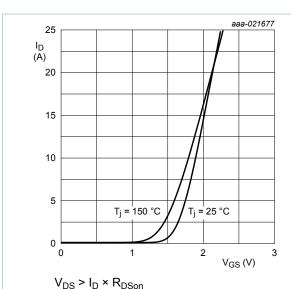


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

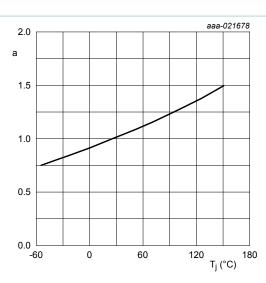


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

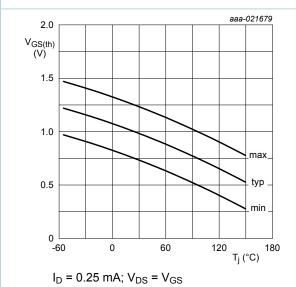
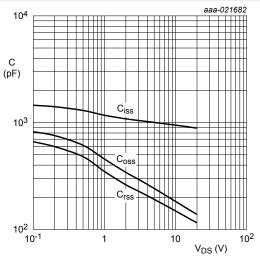


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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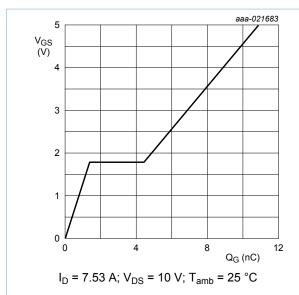


Fig. 14. Gate-source voltage as a function of gate charge; typical values

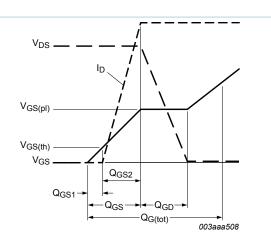


Fig. 15. MOSFET transistor: Gate charge waveform definitions

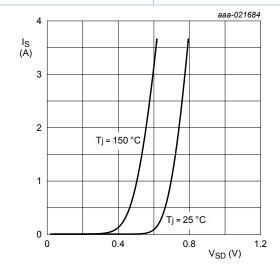
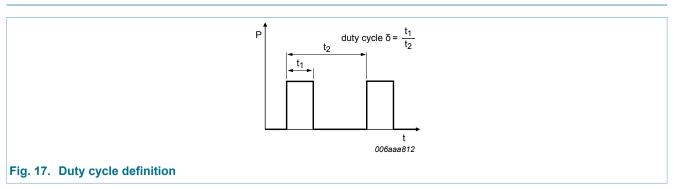


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



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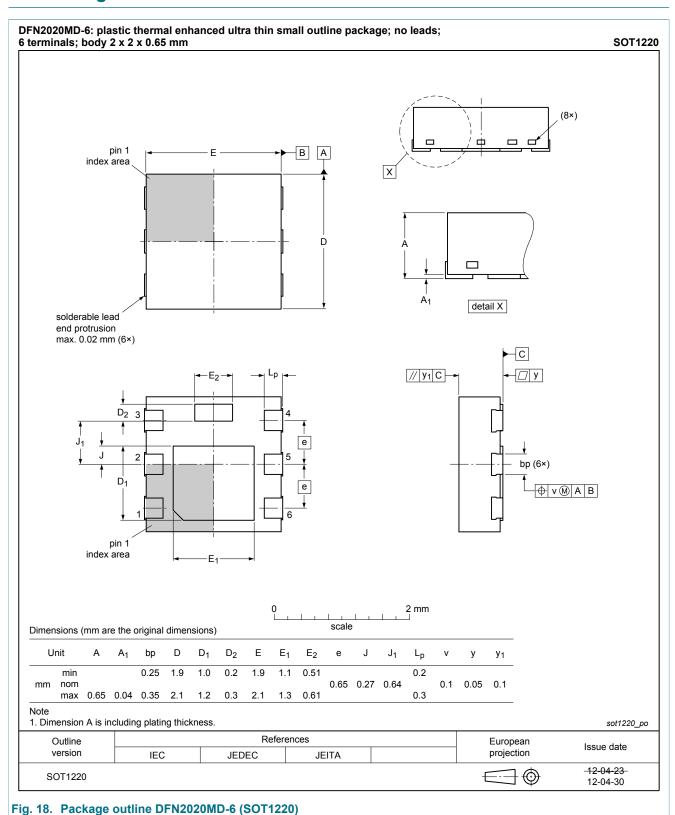
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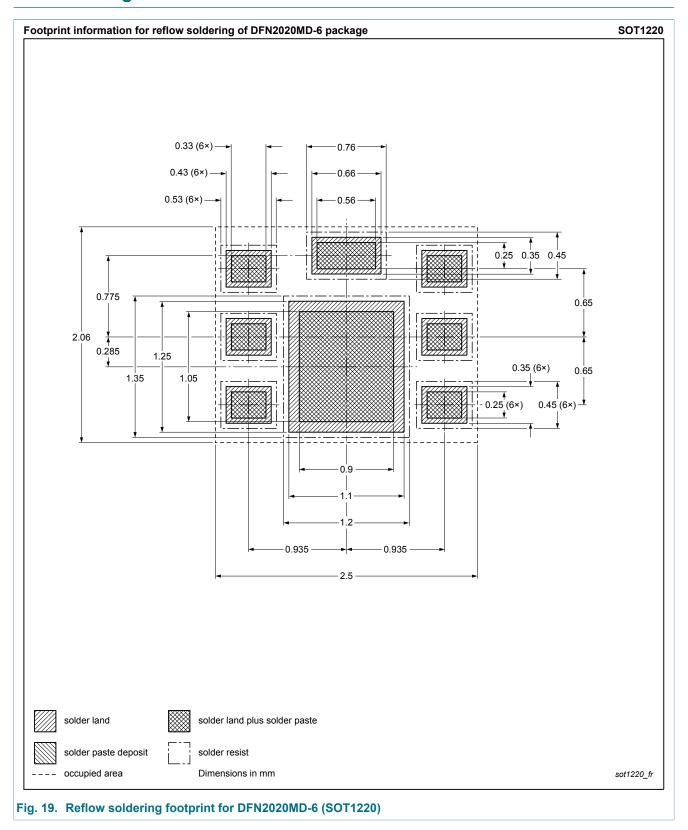
# 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 12. Package outline



# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB20XNEA v.1	20160222	Product data sheet	-	-

#### 20 V, N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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